

N-channel 80 V 41 mΩ logic level MOSFET in LFPAK56

1 May 2013

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in LFPAK56 package. This product has been designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive
- LFPAK56 package is footprint compatible with other Power-SO8 types
- Qualified to 175 °C

3. Applications

- DC-to-DC converters
- Load switch
- TV power supplies

4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	-	25	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	64	W
Static chara	acteristics	· · · · · ·				
R _{DSon}	R _{DSon} drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	32.8	41	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	103	mΩ
Dynamic ch	naracteristics	·	 			
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 5 A; V _{DS} = 64 V;	-	4.3	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 14; Fig. 15</u>	-	21.9	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 25 \text{ A};$ $V_{sup} \leq 80 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped};$ $\overline{\text{Fig. 3}}$		-	-	23.9	mJ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G L F A
4	G	gate	ប្រុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PSMN041-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN041-80YL	04180

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

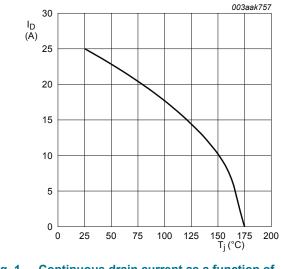
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	18	А
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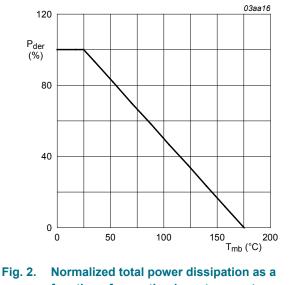
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Symbol	Parameter	Conditions	Min	Max	Unit
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	25	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 4	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	64	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	in diode		I		
I _S	source current	T _{mb} = 25 °C	-	54	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	100	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	23.9	mJ

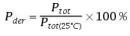




 $V_{GS} \ge 10V$

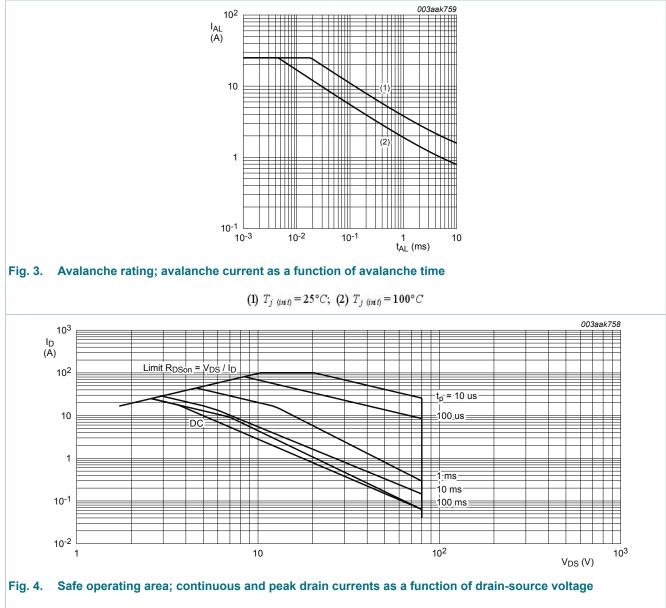






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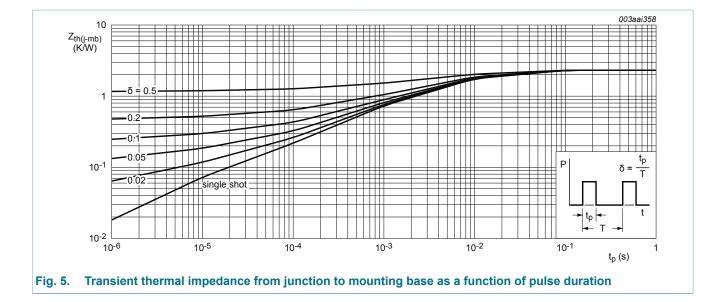


 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.13	2.33	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10; Fig. 11	1.4	1.7	2.1	V	
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; Fig. 12	-	32.8	41	mΩ
resistance	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	113	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	103	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	35.7	45	mΩ
R _G	gate resistance	f = 1 MHz	-	2.02	-	Ω

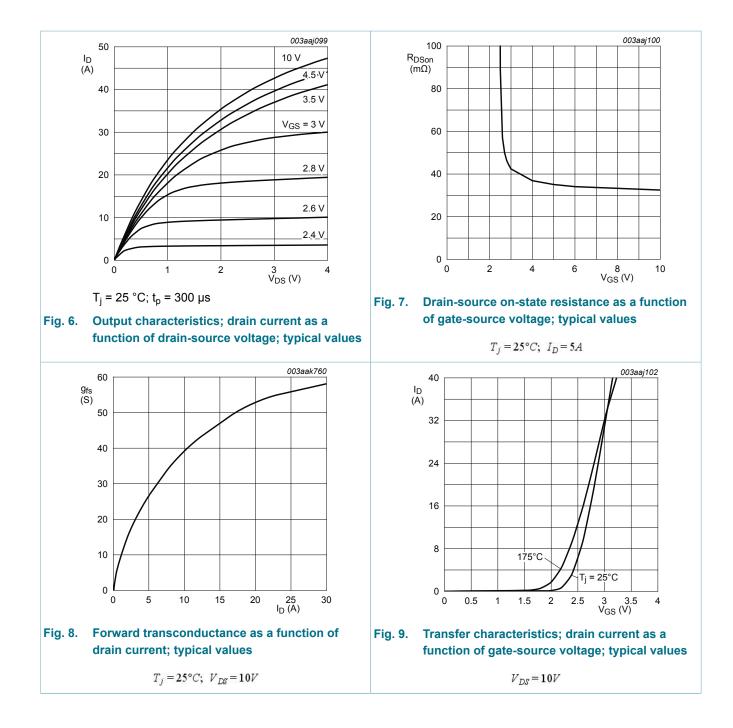
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic ch	haracteristics	· · · · · ·	I			
Q _{G(tot)}	total gate charge	$I_{D} = 5 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{Fig. 14}; \underline{Fig. 15}$	-	21.9	-	nC
		$I_D = 5 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 14}; \text{ Fig. 15}$	-	11.9	-	nC
Q _{GS}	gate-source charge	I _D = 5 A; V _{DS} = 64 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.5	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	1.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	0.8	-	nC
Q _{GD}	gate-drain charge		-	4.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 5 A; V _{DS} = 64 V; T _j = 25 °C; Fig. 14; Fig. 15	-	2.4	-	V
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>	-	1180	-	pF
C _{oss}	output capacitance		-	99	-	pF
C _{rss}	reverse transfer capacitance		-	54	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 10 Ω; V _{GS} = 5 V;	-	8.6	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	11.2	-	ns
t _{d(off)}	turn-off delay time		-	16.1	-	ns
t _f	fall time	1	-	10.5	-	ns
Source-dra	in diode		1	1		
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I_{S} = 5 A; dI _S /dt = 100 A/µs; V _{GS} = 0 V;	-	21.3	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	22	-	nC

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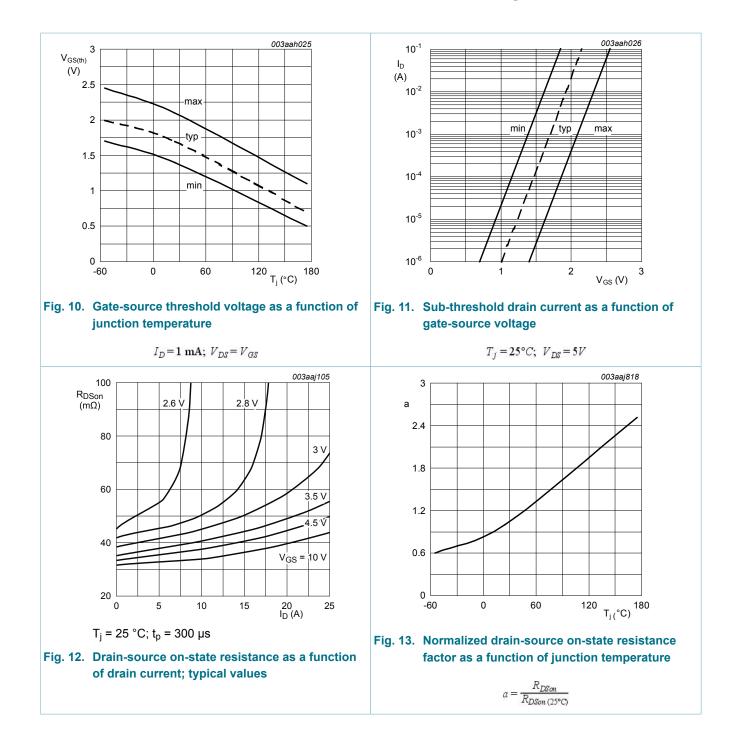
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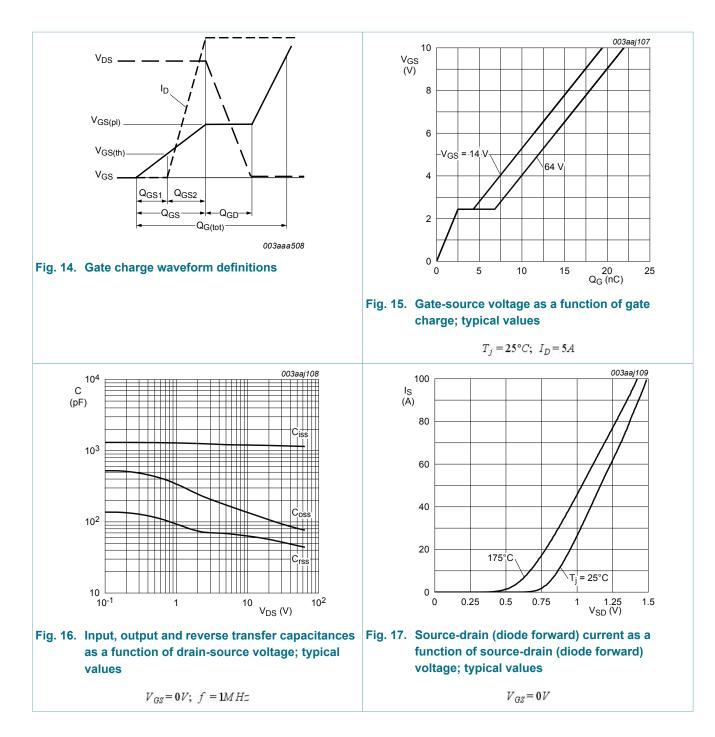
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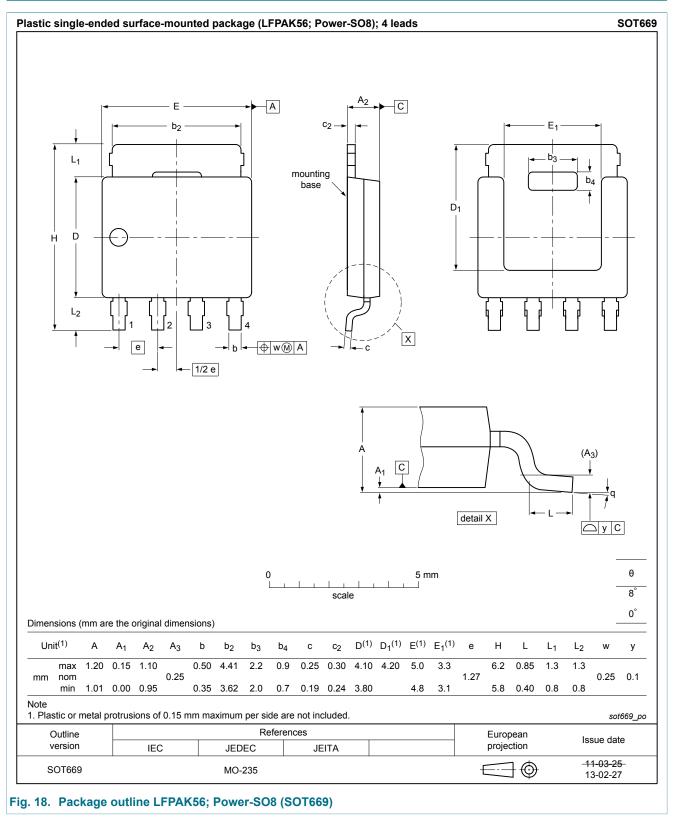


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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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